

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S88	0	"chip-on-chip" same (project\$6) near15 inactive	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:46
S87	0	"chip-on-chip" same (project\$6) near15 height	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:46
S86	58141	chip near2 chip or "chip-on-chip" same (project\$6) near15 height	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:46
S85	58141	chip near2 chip or "chip-on-chip" same (project\$6) near15 inactive	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:46
S92	0	chip\$3chip same (project\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:47
S91	0	chip near2 "on" near2 chip same (project\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:47
S90	0	"chip on chip" same (project\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:47
S89	0	"chip on chip" same (project\$6) near15 inactive	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:47
S95	4	chip\$5chip same electrode near5 height	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:49
S93	47	chip\$5chip same (project\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:49

S84	7	kazutaka near2 shibata.in. and chip\$1on\$1chip same resin and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:12
S56	46	(Kazutaka near2 Shibata).in. and chip\$1on\$1chip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:12
S16	30	semiconductor near3 chip same resin same electrode same (polish\$ or grind\$) same (rear or back)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:12
S8	176	resin near10 (back or back\$1sid\$) same (polish\$ or grind\$) and semiconduct\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:12
S7	453	(resin same (polish\$ or grind\$)) same (back or back\$1sid\$) and semiconduct\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:12
L5	46	semiconductor near3 chip same resin same electrode same (polish\$ or grind\$) same (rear or back)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:12
L4	716	(resin same (polish\$ or grind\$)) same (back or back\$1sid\$) and semiconduct\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:12
L3	276	resin near10 (back or back\$1sid\$) same (polish\$ or grind\$) and semiconduct\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:12
L2	7	kazutaka near2 shibata.in. and chip\$1on\$1chip same resin and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:12
L1	55	(Kazutaka near2 Shibata).in. and chip\$1on\$1chip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:12

S94	117	chip\$5chip same electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:13
L6	117	chip\$5chip same electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 18:13